

ISL3034E

6-Channel High Speed, Auto-Direction Sensing Logic Level Translator

FN6492
Rev.2.00
Nov 7, 2019

The [ISL3034E](#) is a 6-channel bidirectional, auto-direction sensing, level translator that provides the required level shifting in multi-voltage systems at data transfer rates up to 100Mbps. The auto-direction sensing feature makes the ISL3034E ideally suited for generic six channel level translation especially if bit-by-bit direction control is desired. The V_{CC} and V_L supply voltages set the logic levels on either side of the device. Logic signals on the IC's V_L side appear as higher voltage logic signals on the IC's V_{CC} side. Logic signals on the IC's V_{CC} side appear as higher voltage logic signals on the IC's V_L side.

The ISL3034E operates at full speed with external input drivers that source as little as 4mA output current. Each I/O channel is pulled up to V_{CC} or V_L by an internal 30 μ A current source, allowing the ISL3034E to be driven by either push-pull or open-drain drivers.

Drive the ISL3034E's enable (EN) input low to place the IC into a low-power shutdown mode with all I/O lines tri-stated. The device features an automatic shutdown mode that places the part in the same shutdown state when V_{CC} is less than V_L .

The ISL3034E operates with V_{CC} voltages from +2.2V to +3.6V and V_L voltages from +1.35V to +3.2V, making it ideal for data transfer between low-voltage microcontrollers or ASICs and higher voltage components.

Related Literature

For a full list of related documents, visit our website:

- [ISL3034E](#) device page

Features

- Best-In-Class ESD protection: ± 15 kV IEC61000-4-2 ESD protection on all input, output, and I/O lines
- 100Mbps ensured data rate
- Six bidirectional channels
- Auto-direction sensing eliminates direction control logic pins
- Enable input for logic control of low power SHDN Mode
- Compatible with 4mA input drivers or larger
- +1.35V $\leq V_L \leq$ +3.2V and +2.2V $\leq V_{CC} \leq$ +3.6V supply voltage range
- Pb-Free (RoHS compliant)
- 16Ld μ TQFN (2.6mmx1.8mm) and 16 Ld TQFN (3mmx3mm) packages

Applications

- Simplifies the interface between two logic ICs operating at different supply voltages

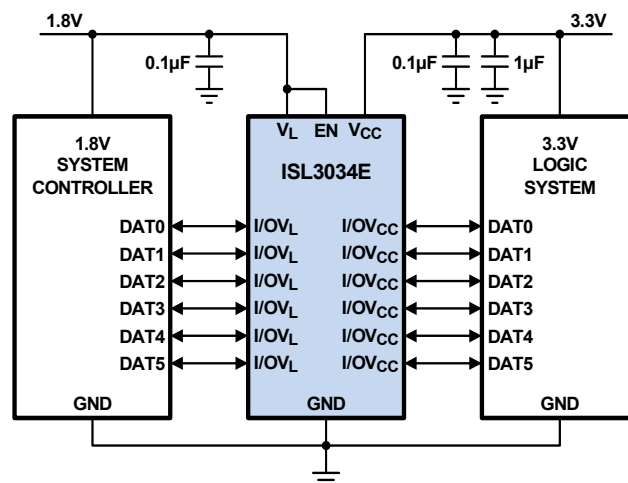


FIGURE 1. TYPICAL OPERATING CIRCUIT

TABLE 1. SUMMARY OF FEATURES

PART NUMBER	DATA RATE (Mbps)	NUMBER OF CHANNELS	EN PIN?	I/OV _L SHDN STATE	I/OV _{CC} SHDN STATE
ISL3034E	100	6	YES	16.5k to V_L	16.5k Ω to V_{CC}

Ordering Information

PART NUMBER (Note 4)	PART MARKING	TEMP. RANGE (°C)	TAPE AND REEL (UNITS) (Note 3)	PACKAGE (RoHS Compliant)	PKG. DWG. #
ISL3034EIRTZ (Note 1)	34TZ	-40 to +85	-	16 Ld TQFN	L16.3x3A
ISL3034EIRTZ-T (Note 1)	34TZ	-40 to +85	6k	16 Ld TQFN	L16.3x3A
ISL3034EIRUZ-T (Note 2)	GAE	-40 to +85	3k	16 Ld UTQFN	L16.2.6x1.8A

NOTES:

- These Pb-free plastic packaged products employ special Pb-free material sets, molding compounds/die attach materials, and 100% matte tin plate plus anneal (e3 termination finish, which is RoHS compliant and compatible with both SnPb and Pb-free soldering operations). Pb-free products are MSL classified at Pb-free peak reflow temperatures that meet or exceed the Pb-free requirements of IPC/JEDEC J STD-020.
- These Pb-free plastic packaged products employ special Pb-free material sets; molding compounds/die attach materials and NiPdAu plate - e4 termination finish, which is RoHS compliant and compatible with both SnPb and Pb-free soldering operations. Pb-free products are MSL classified at Pb-free peak reflow temperatures that meet or exceed the Pb-free requirements of IPC/JEDEC J STD-020.
- Refer to [TB347](#) for details about reel specifications.
- For Moisture Sensitivity Level (MSL), see the [ISL3034E](#) product information page. For more information about MSL, see [TB363](#).

Pin Configuration



Pin Descriptions

NAME	FUNCTION
V _{CC}	V _{CC} power supply, +2.2V to +3.6V. Decouple V _{CC} to ground with a 0.1μF capacitor.
V _L	V _L logic supply, +1.35V to +3.2V. Decouple V _L to ground with a 0.1μF capacitor.
GND	Ground Pin
EN	±15kV IEC61000 ESD Protected Enable Input. Logic "0" puts the device in shutdown. Logic "1" enables the device.
I/OV _{CC} x	±15kV IEC61000 ESD Protected Input/Output channel referenced to V _{CC} .
I/OV _L x	±15kV IEC61000 ESD Protected Input/Output channel referenced to V _L .

Absolute Maximum Ratings

(All voltages referenced to GND.)

V_{CC}, V_L	-0.3V to +4V
I/OV_{CC}	-0.3V to ($V_{CC} + 0.3V$)
I/OV_L	-0.3V to ($V_L + 0.3V$)
EN	-0.3V to +4V
Short-Circuit Duration $I/OV_L, I/OV_{CC}$ to GND	Continuous

Thermal Information

Thermal Resistance (Typical)	θ_{JA} (°C/W)	θ_{JC} (°C/W)
16 Ld TQFN Package (Notes 5, 6)	74	10
16 Ld UTQFN Package (Notes 5, 6)	93	44
Maximum Junction Temperature (Plastic Package)	+150°C	
Storage Temperature Range	-65°C to +150°C	
Pb-Free Reflow Profile	see TB493	

Operating Conditions

Operating Temperature Range -40°C to +85°C

CAUTION: Do not operate at or near the maximum ratings listed for extended periods of time. Exposure to such conditions may adversely impact product reliability and result in failures not covered by warranty.

NOTES:

- θ_{JA} is measured with the component mounted on a high-effective thermal conductivity test board in free air, and with “direct attach” features for the QFN and TQFN. See TB379 for details.
- For θ_{JC} , the “case temp” location is the center of the exposed metal pad on the package underside.

Electrical Specifications $V_{CC} = +2.2V$ to $+3.6V$, $V_L = +1.35V$ to $+3.2V$, EN = V_L , unless otherwise noted. Typical values are at $V_{CC} = +3.3V$, $V_L = +1.8V$ and $T_A = +25^\circ C$. (Note 7).

PARAMETER	SYMBOL	TEST CONDITIONS	TEMP (°C)	MIN (Note 9)	TYP	MAX (Note 9)	UNITS
POWER SUPPLIES							
V_L Supply Range	V_L	(Note 7)	Full	1.35	-	3.2	V
V_{CC} Supply Range	V_{CC}	(Note 7)	Full	2.2	-	3.6	V
V_{CC} Quiescent Supply Current	I_{CC}	$I/OV_{CC} = V_{CC}, I/OV_L = V_L$	Full	-	18	30	μA
V_L Quiescent Supply Current	I_{VL}	$I/OV_{CC} = V_{CC}, I/OV_L = V_L$	Full	-	12	18	μA
V_{CC} Shutdown Supply Current	I_{CCSD}	EN = GND or $V_L > V_{CC} + 0.7V$	Full	-	-	2.5	μA
V_L Shutdown Supply Current	I_{LSD}	EN = GND or $V_L > V_{CC} + 0.7V$	Full	-	-	4	μA
EN Input Current	I_{IN_EN}		Full	-		1	μA
$V_L - V_{CC}$ Shutdown Threshold High	V_{TH_H}	V_{CC} rising	Full	-0.2	$0.05V_L$	0.7	V
$V_L - V_{CC}$ Shutdown Threshold Low	V_{TH_L}	V_{CC} falling	Full	-0.2	$0.1V_L$	0.7	V
$I/OV_{CC}, I/OV_L$ Pull-Up Resistance During Shutdown	R_{PU_SD1}	EN = GND	Full	10	16.5	23	kΩ
I/OV_L Pull-Up Current	I_{VL_PU}	EN = V_L , $I/OV_L = GND$	Full	20	-	75	μA
I/OV_{CC} Pull-Up Current	I_{VCC_PU}	EN = V_L , $I/OV_{CC} = GND$	Full	20	-	75	μA
I/OV_L to I/OV_{CC} DC Resistance	R_{ON}		Full	-	3	-	kΩ
ESD PROTECTION							
All Input and I/O Pins From Pin to GND		IEC61000-4-2 Air-Gap Discharge	25	-	±15	-	kV
		IEC61000-4-2 Contact Discharge	25	-	≥±9	-	kV
		Human Body Model	25	-	±15	-	kV
All Pins		HBM, per JEDEC	25	-	≥±12	-	kV
		Machine Model, per JEDEC	25	-	±1300	-	V

Electrical Specifications $V_{CC} = +2.2V$ to $+3.6V$, $V_L = +1.35V$ to $+3.2V$, $EN = V_L$, unless otherwise noted. Typical values are at $V_{CC} = +3.3V$, $V_L = +1.8V$ and $T_A = +25^\circ C$. (Note 7). (Continued)

PARAMETER	SYMBOL	TEST CONDITIONS	TEMP (°C)	MIN (Note 9)	TYP	MAX (Note 9)	UNITS	
LOGIC-LEVEL THRESHOLDS								
I/OV _L Input Voltage High Threshold	V _{IHL}	(Note 8)	Full	-	-	V _L - 0.2	V	
I/OV _L Input Voltage Low Threshold	V _{ILL}	(Note 8)	Full	0.15	-	-	V	
I/OV _{CC} Input Voltage High Threshold	V _{IHC}	(Note 8)	Full	-	-	V _{CC} - 0.4	V	
I/OV _{CC} Input Voltage Low Threshold	V _{ILC}	(Note 8)	Full	0.2	-	-	V	
EN Input Voltage High Threshold	V _{IH}		Full	-	-	V _L - 0.4	V	
EN Input Voltage Low Threshold	V _{IL}		Full	0.4	-	-	V	
I/OV _L Output Voltage High	V _{OHL}	I _{OH} = 20μA, I/OV _{CC} ≥ V _{CC} - 0.4V	Full	2/3 V _L	-	-	V	
I/OV _L Output Voltage Low	V _{OLL}	I _{OL} = 20μA, I/OV _{CC} ≤ 0.2V	Full	-	-	1/3 V _L	V	
I/OV _{CC} Output Voltage High	V _{OHC}	I _{OH} = 20μA, I/OV _L ≥ V _L - 0.2V	Full	2/3 V _{CC}	-	-	V	
I/OV _{CC} Output Voltage Low	V _{OLC}	I _{OL} = 20μA, I/OV _L ≤ 0.15V	Full	-	-	1/3 V _{CC}	V	
RISE/FALL TIME ACCELERATOR STAGE								
Accelerator Pulse Duration		On falling edge	25	-	3	-	ns	
		On rising edge	25	-	3	-	ns	
I/OV _L Output Accelerator Source Impedance		V _L = 1.62V	25	-	11	-	Ω	
		V _L = 3.2V	25	-	6	-	Ω	
I/OV _{CC} Output Accelerator Source Impedance		V _{CC} = 2.2V	25	-	9	-	Ω	
		V _{CC} = 3.6V	25	-	8	-	Ω	
I/OV _L Output Accelerator Sink Impedance		V _L = 1.62V	25	-	9	-	Ω	
		V _L = 3.2V	25	-	8	-	Ω	
I/OV _{CC} Output Accelerator Sink Impedance		V _{CC} = 2.2V	25	-	10	-	Ω	
		V _{CC} = 3.6V	25	-	9	-	Ω	
TIMING CHARACTERISTICS (R _{SOURCE} = 150Ω, Input rise/fall time ≤ 1ns)								
I/OV _{CC} Rise Time	t _{RVCC}	R _S = 150Ω, C _{I/OVCC} = 10pF, push-pull drivers		Full	-	-	3.2	ns
I/OV _{CC} Fall Time	t _{FVCC}	R _S = 150Ω, C _{I/OVCC} = 10pF		Full	-	-	3.2	ns
I/OV _L Rise Time	t _{RVL}	R _S = 150Ω, C _{I/OVL} = 15pF, push-pull drivers	V _L ≥ 1.35V	Full	-	-	4	ns
			V _L ≥ 1.62V	Full	-	-	3.5	ns
I/OV _L Fall Time	t _{FVL}	R _S = 150Ω, C _{I/OVL} = 15pF	V _L ≥ 1.35V	Full	-	-	4	ns
			V _L ≥ 1.62V	Full	-	-	3.5	ns
I/OV _{CC} Propagation Delay (Driving I/OV _L)	t _{PDVCC}	R _S = 150Ω, C _{I/OVCC} = 10pF, push-pull drivers	V _L ≥ 1.35V	Full	-	-	7.5	ns
			V _L ≥ 1.62V	Full	-	-	6.5	ns
t _{PDVCC} Channel-to-Channel Skew (Note 10)	t _{SKEWC}		V _L ≥ 1.35V	Full	-	-	1.3	ns
			V _L ≥ 1.62V	Full	-	-	1	ns
I/OV _L Propagation Delay (Driving I/OV _{CC})	t _{PDVL}	R _S = 150Ω, C _{I/OVL} = 15pF, push-pull drivers		Full	-	-	6.5	ns
t _{PDVL} Channel-to-Channel Skew (Note 10)	t _{SKEWL}		V _L ≥ 1.35V	Full	-	-	1.3	ns
			V _L ≥ 1.62V	Full	-	-	0.8	ns

Electrical Specifications $V_{CC} = +2.2V$ to $+3.6V$, $V_L = +1.35V$ to $+3.2V$, $EN = V_L$, unless otherwise noted. Typical values are at $V_{CC} = +3.3V$, $V_L = +1.8V$ and $T_A = +25^\circ C$. (Note 7). (Continued)

PARAMETER	SYMBOL	TEST CONDITIONS	TEMP ($^\circ C$)	MIN (Note 9)	TYP	MAX (Note 9)	UNITS
Delay from EN High to I/OV _{CC} Active	t_{EN-VCC}	$R_{LOAD} = 1M\Omega$, $C_{I/OVCC} = 10pF$	25	-	1.5	-	μs
Delay from EN High to I/OV _L Active	t_{EN-VL}	$R_{LOAD} = 1M\Omega$, $C_{I/OVL} = 15pF$	25	-	1.5	-	μs
Maximum Data Rate	D.R.1.35	Push-pull operation, $R_{SOURCE} = 150\Omega$, $C_{I/OVCC} = 10pF$, $C_{I/OVL} = 15pF$,	$V_L \geq 1.35V$	Full	85	-	Mbps
	D.R.1.6		$V_L \geq 1.62V$	Full	100	-	Mbps

- NOTES:
- 7. V_L must be less than or equal to $V_{CC} - 0.2V$ during normal operation. However, V_L can be greater than V_{CC} during start-up and shutdown conditions and the part will not latch-up nor be damaged.
 - 8. Input thresholds are referenced to the boost circuit.
 - 9. Parameters with MIN and/or MAX limits are 100% tested at $+25^\circ C$, unless otherwise specified. Temperature limits established by characterization and are not production tested.
 - 10. Delta between all I/OV_L channel prop delays, or delta between all I/OV_{CC} channel prop delays, all channels tested at the same test conditions.

Test Circuits and Waveforms

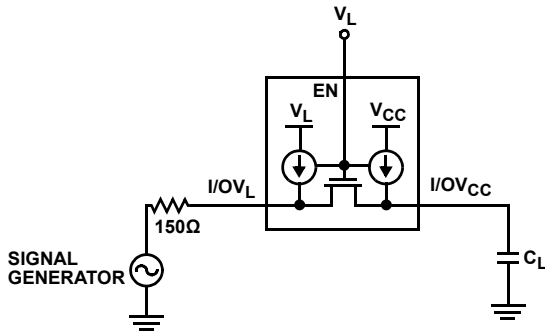


FIGURE 2A. TEST CIRCUIT

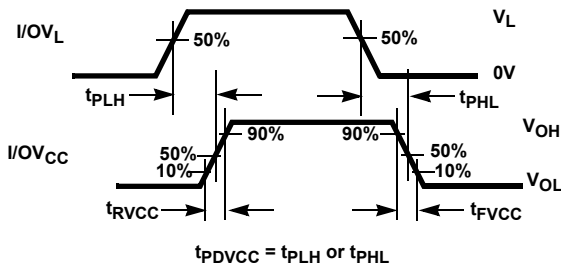


FIGURE 2B. MEASUREMENT POINTS

FIGURE 2. I/OV_{CC} OUTPUT PROPAGATION DELAY AND TRANSITION TIMES (PUSH - PULL)

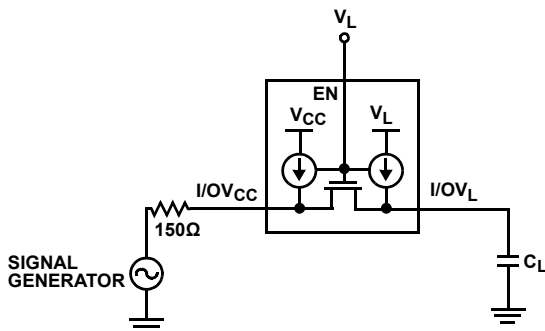


FIGURE 3A. TEST CIRCUIT

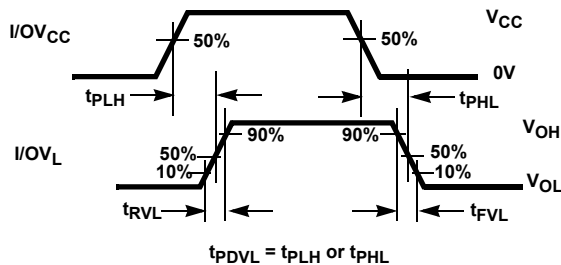


FIGURE 3B. MEASUREMENT POINTS

FIGURE 3. I/OV_L OUTPUT PROPAGATION DELAY AND TRANSITION TIMES (PUSH - PULL)

Test Circuits and Waveforms (Continued)

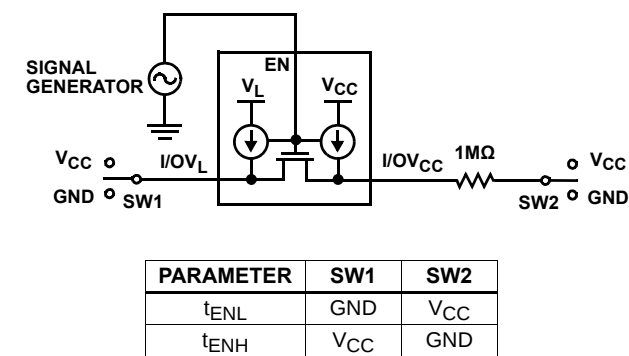


FIGURE 4A. TEST CIRCUIT

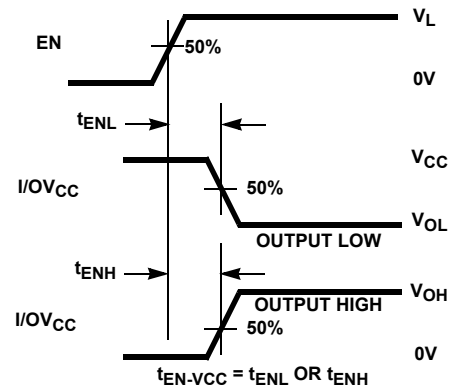


FIGURE 4B. MEASUREMENT POINTS

FIGURE 4. I/OV_{CC} OUTPUT ENABLE TIMES

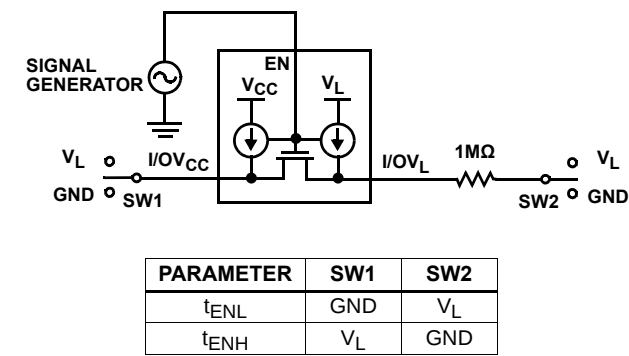


FIGURE 5A. TEST CIRCUIT

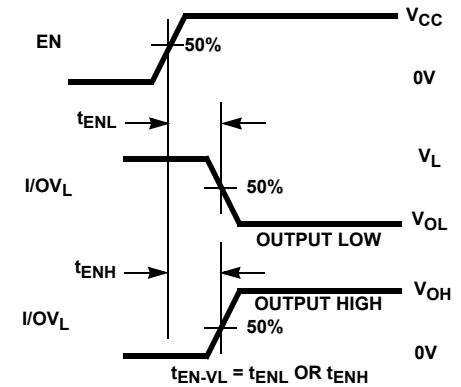


FIGURE 5B. MEASUREMENT POINTS

FIGURE 5. I/OV_L OUTPUT ENABLE TIMES

Application Information

Overview

The ISL3034E is a 100Mbps, bidirectional voltage level translating IC for multi-supply voltage systems. The device shifts lower voltage levels on one interface side (supplied by V_L) to a higher voltage level on the other interface side (supplied by V_{CC}), or vice versa. V_{OH} of the I/OV_L pins tracks the V_L supply, while V_{OH} of the I/OV_{CC} pins tracks the V_{CC} supply.

The ISL3034E features bit-by-bit auto-direction sensing to increase flexibility and eliminate the need for direction control pins. On-chip pull-up current sources in the active mode and pull-up resistors in SHDN mode eliminate the need for most external bus resistors. Open-drain or push-pull type drivers can interface with this level translator, and the device can also be used for unidirectional level shifting.

The ISL3034E is a general purpose 6-Channel level translator. Power supply ranges allow level shifting between 1.5V, 1.8V, and 2.5V powered devices on the V_L side to 2.5V and 3.3V devices on the V_{CC} side.

Principles of Operation

When enabled, the level shifter detects transitions on an I/O pin and drives the appropriate logic level on the corresponding I/O pin on the other “side”. If the transition was low-to-high, the channel shifts the voltage up to V_{CC} (for transitions on an I/OV_L pin) or down to V_L (for transitions on an I/OV_{CC} pin), and then drives the shifted level on the other side. The ISL3034E enables when $EN = 1$ AND $V_{CC} > V_L + 200mV$.

Upon detecting a transition on either I/O pin, that channel's accelerator circuitry actively drives the opposite side's (output) pin to GND or the output's supply rail, then turns off. Weak hold circuitry then maintains the logic state until the input is tri-stated, or until another active transition occurs on either I/O pin for that channel. [Figure 6 on page 7](#) shows the simplified block diagram of one level shifting channel.

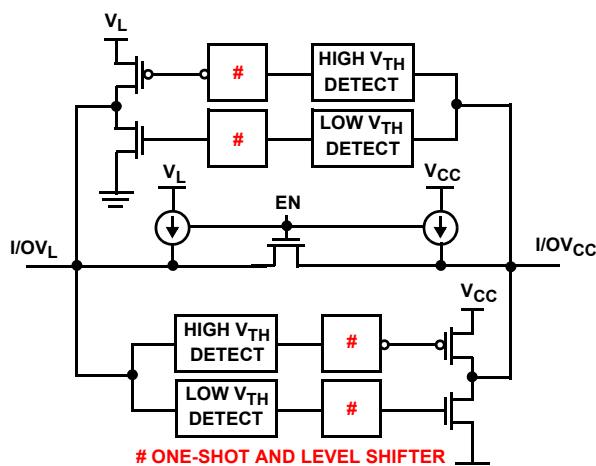


FIGURE 6. ONE CHANNEL SIMPLIFIED SCHEMATIC

The accelerator circuitry comprises high and low threshold detectors, one-shots with level shifters, and large output drivers. A transition on one of the I/OV_L or I/OV_{CC} pins momentarily defines that pin as an input. When the high or low threshold is crossed, a one-shot fires either the PMOS or NMOS driver, respectively, on the opposite side (effectively the output). These drivers are large enough to quickly drive the output node to its respective supply or to GND. Note that this transition on the “output” trips the transition detector on that pin, firing its accelerator, which feeds back to the “input” to help reinforce slow transitions, such as those from an open-drain type driver. When the one-shot (and thus the accelerator) times out (approximately 3ns to 4ns), the large output drivers tri-state and the pins are weakly held in the last state by the small NMOS transistor between I/OV_L and I/OV_{CC} (for a low) or by the small current sources (for a high). In this static state, the I/O pins are easily overdriven by the next transition from an external driver. Having large pull-up and pull-down devices in the accelerator (vs just an active pull-up) nearly eliminates the concern about the external driver's output impedance, and that impedance's effect on V_{OL} , fall times, and data rate.

The weak pull-up current sources on each I/O pin and the NMOS pass transistors remain ON whenever the IC is enabled. If a channel's external driver tri-states, the weak pull-up currents either keep the I/O pins high, or the current sources pull the I/O pins high if the last state was a low. In the latter case, each channel's accelerators once again fire when either the I/OV_L or the I/OV_{CC} voltage crosses the accelerator's high threshold level.

Auto Direction Sensing

Each level translator channel independently and automatically determines the direction of data transfer without any external control signals. As described in [“Principles of Operation” on page 7](#), a transition on either of the channel's I/O pins momentarily defines that pin as an input, which then translates and drives that input signal to the channel's corresponding pin on the other port (now the output). After a brief period of active driving, both I/O pins return to their weak “hold” mode, in which the next transition on either I/O pin determines the direction for the next transfer.

Auto sensing saves valuable processor GPIO pins and simplifies the software associated with the peripheral interface.

Using Open Drain Drivers

The level translators' accelerator based architecture works equally well when driven by push-pull or open drain type drivers. The low static pull-up current is easily overdriven by an active pull-down, and the feedback nature of the accelerators (that is, the accelerator firing in one direction also triggers the accelerator in the opposite direction) aids the passive pull-up when the input signal passes the accelerator's high threshold. The pull-up current and load capacitance set the input signal rise time, and thus the maximum data rate. For slow data rates the internal pull-up current may suffice, but higher data rates or more heavily loaded signal lines may require an external pull-up resistor.

Using External Bus Resistors

As mentioned in “Overview” on page 7, the ISL3034E incorporates I/O pin pull-up current sources when enabled, and I/O pin pull-up resistors in SHDN mode. Therefore, external pull-up or pull-down resistors are not necessary, and are not recommended, unless using high-speed open drain signaling.

Power Supplies

WIDE SUPPLY RANGE

The device operates across a wide range of supply voltages. V_L is designed to connect to the supply of 1.5V, 1.8V, and 2.5V powered devices, while V_{CC} is targeted for 2.5V and 3.3V components. Note that V_{CC} must be greater than V_L for proper operation.

POWER SUPPLY SEQUENCING

Either V_{CC} or V_L can be powered up first, but the IC remains in SHDN until V_{CC} exceeds V_L by as much as 200mV. V_L may exceed V_{CC} by as much as 4V without causing any damage.

I/O PIN INPUT THRESHOLDS VS SUPPLY VOLTAGE

Although the “Electrical Specifications” table on page 4 shows the I/O pin input thresholds (V_{IH} , V_{IL}) with a fixed delta from the supplies or GND, the thresholds are better represented as a percentage of the supplies. The typical $I/O_{V_{CC}} V_{IH}$ runs about 55% to 60% of V_{CC} , while the corresponding V_{IL} runs about 33% of V_{CC} . The typical $I/O_{V_L} V_{IH}$ runs about 60% to 70% of V_L , while the corresponding V_{IL} runs about 25% to 35% of V_L .

Low Power SHDN Mode

The ISL3034E features a low power SHDN mode that tri-states all the I/O and output pins, considerably reduces current consumption, and enables any pull-up resistors on a port's I/O pins (see Table 1 on page 1). The device enters SHDN mode when the EN input switches low, or automatically when the V_{CC} voltage drops below the V_L voltage. The V_L supply powers the EN circuitry.

Unidirectional Level Translator with Heavy Loading

In applications where the ISL3034E is used as an unidirectional level translator, care must be taken to provide sufficient current drive if the output is heavily loaded. Figure 7 depicts a circuit where the output is loaded by some 500Ω. In this case, no matter

how well V_{CC} is buffered, the output oscillates, and the device might even turn into a latch-up condition. The internal feedback structure of the ISL3034E also causes this oscillation to appear at the input side (Figure 8).

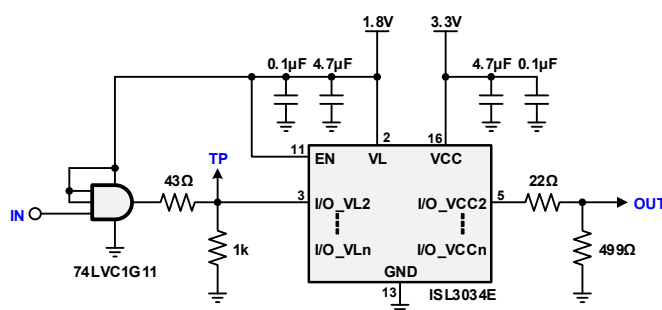


FIGURE 7. LOAD UNIDIRECTIONAL LEVEL TRANSLATOR WITH HEAVY LOADING OF THE UNBUFFERED OUTPUT

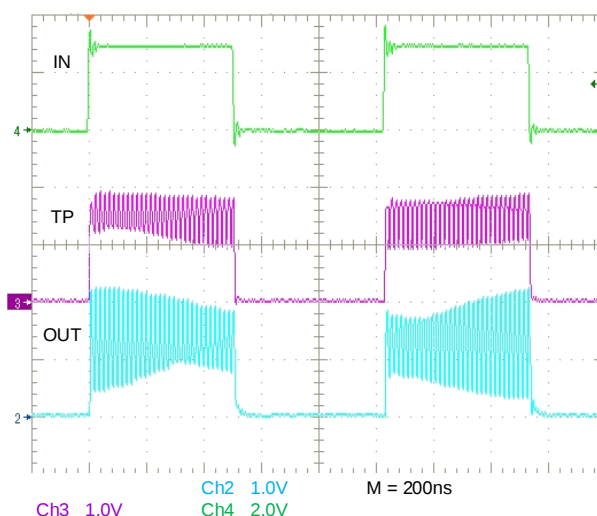


FIGURE 8. SIGNAL WAVEFORMS AT THE VARIOUS TEST POINTS OF THE CIRCUIT IN Figure 7

Figure 9 and Figure 10 show that to prevent the output from oscillations and latch-up conditions, a logic gate driver with enough current drive is inserted between the IC output and the low-impedance load.

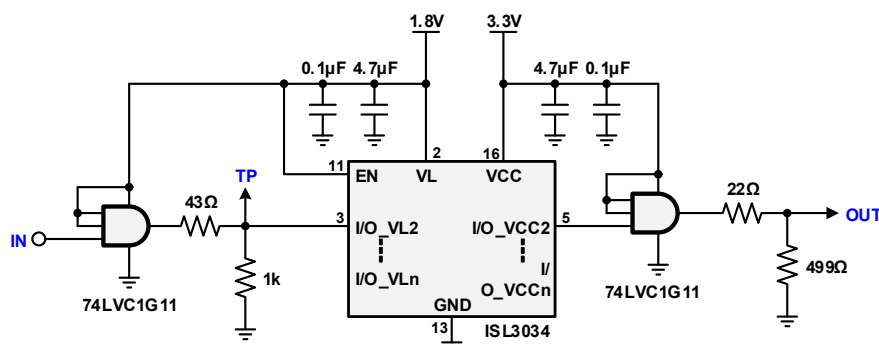


FIGURE 9. LOAD UNIDIRECTIONAL LEVEL TRANSLATOR WITH HEAVY LOADING OF A BUFFERED OUTPUT

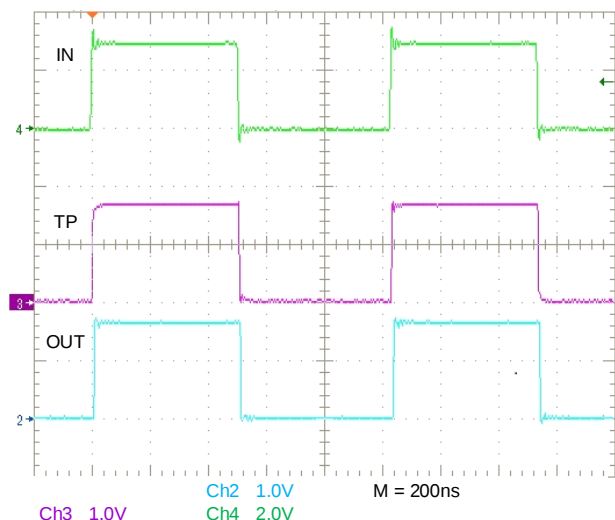


FIGURE 10. SIGNAL WAVEFORMS AT THE VARIOUS TEST POINTS OF THE CIRCUIT IN [Figure 9](#)

Best-in-Class ESD Protection

All pins on the ISL3034E include class 3 (>12kV) Human Body Model (HBM) ESD protection structures, but the input and I/O pins incorporate advanced structures allowing them to survive ESD events in excess of $\pm 15\text{kV}$ HBM and $\pm 15\text{kV}$ to IEC61000-4-2. The I/OV_{CC} pins are particularly vulnerable to ESD damage because they typically connect to an exposed port on the exterior of the finished product. Touching the port pins or connecting a memory card can cause an ESD event that might destroy unprotected ICs. These new ESD structures protect the device whether or not it is powered up and without degrading the level shifting performance. This built-in ESD protection eliminates the need for board level protection structures (for example, transient suppression diodes) and the associated undesirable capacitive load they present. To ensure the full benefit of the built-in ESD protection, connect the IC's GND pin directly to a low impedance GND plane.

IEC61000-4-2 Testing

The IEC61000 test method applies to finished equipment, rather than to an individual IC. Therefore, the pins most likely to suffer an ESD event are those that are exposed to the outside world (typically I/OV_{CC} pins in memory card applications) but the ISL3034E features IEC61000 ESD protection on all logic and I/O pins (both I/OV_L and I/OV_{CC}, as well as CLK pins). Unlike HBM and MM methods which only test each pin-to-pin combination without applying power, IEC61000 testing is also performed with the IC in its typical application configuration (power applied). The IEC61000 standard's lower current limiting resistor coupled with the larger charge storage capacitor yields a test that is much more severe than the HBM test. The extra ESD protection built into the device's pins allows the design of equipment meeting Level 4 criteria without the need for additional board level protection.

AIR-GAP DISCHARGE TEST METHOD

For this test method, a charged probe tip moves toward the IC pin until the voltage arcs to it. The current waveform delivered to the IC pin depends on approach speed, humidity, temperature, etc., so it is difficult to obtain repeatable results. All the EN, and I/O pins withstand $\pm 15\text{kV}$ air-gap discharges, relative to GND.

CONTACT DISCHARGE TEST METHOD

During the contact discharge test, the probe contacts the tested pin before the probe tip is energized, thereby eliminating the variables associated with the air-gap discharge. The result is a more repeatable and predictable test, but equipment limits prevent testing devices at voltages higher than $\pm 9\text{kV}$. The ISL3034E survives $\pm 9\text{kV}$ contact discharges (relative to the GND pin) on the EN, CLK, and I/O pins.

Layout and Decoupling Considerations

This level translator's high data rate and fast signal transitions require that the accelerators have high transient currents. Use short, low inductance supply traces and decouple within $1/8^{\text{th}}$ inch of the IC with very low impedance GND return paths.

Typical Performance Curves

$V_{CC} = 3.3V$, $V_L = 1.8V$, $C_L = 15pF$, $R_{SOURCE} = 150\Omega$, data rate = 100Mbps, push-pull driver, $T_A = +25^\circ C$; unless otherwise specified.

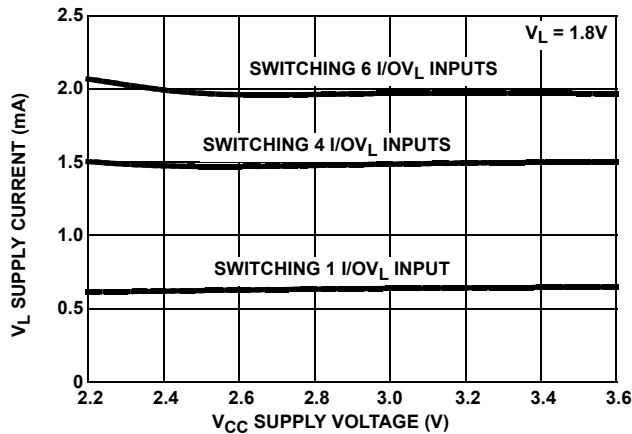


FIGURE 11. V_L SUPPLY CURRENT vs V_{CC} SUPPLY VOLTAGE

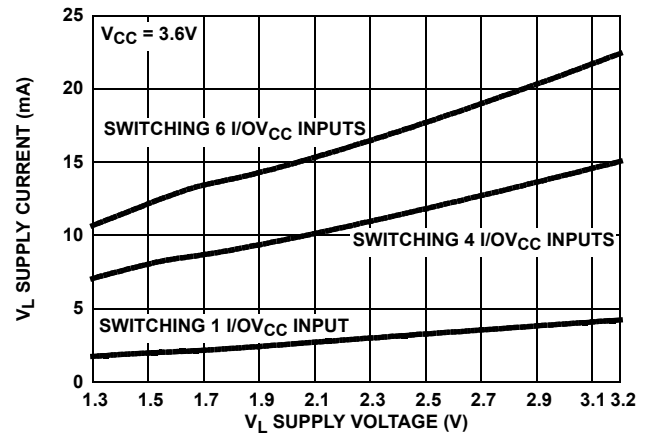


FIGURE 12. V_L SUPPLY CURRENT vs V_L SUPPLY VOLTAGE

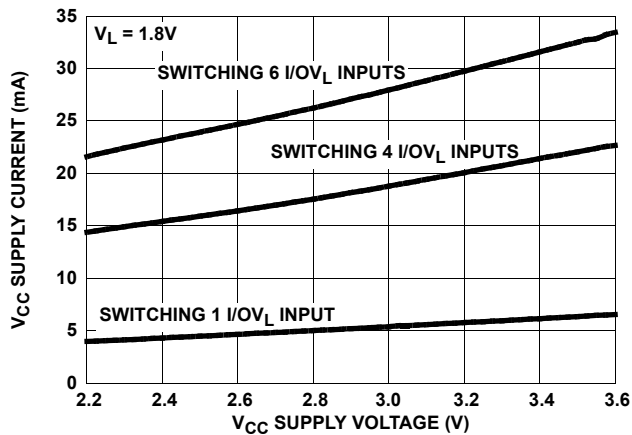


FIGURE 13. V_{CC} SUPPLY CURRENT vs V_{CC} SUPPLY VOLTAGE

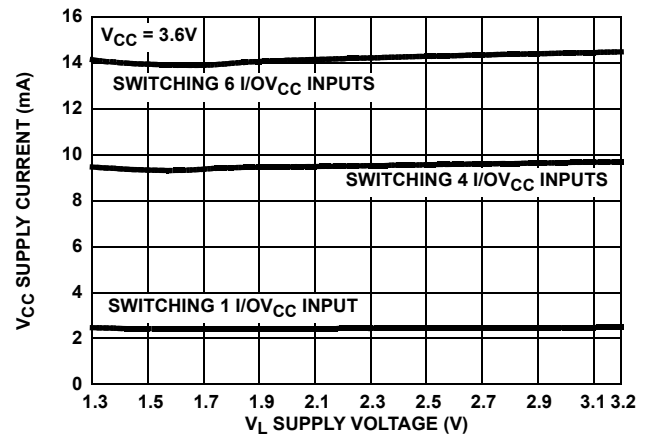


FIGURE 14. V_{CC} SUPPLY CURRENT vs V_L SUPPLY VOLTAGE

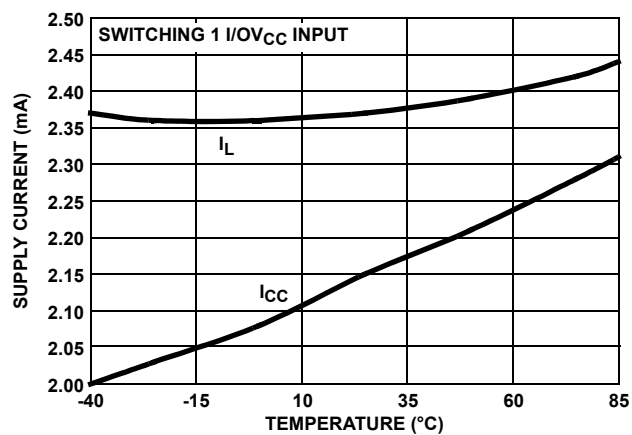


FIGURE 15. SUPPLY CURRENT vs TEMPERATURE

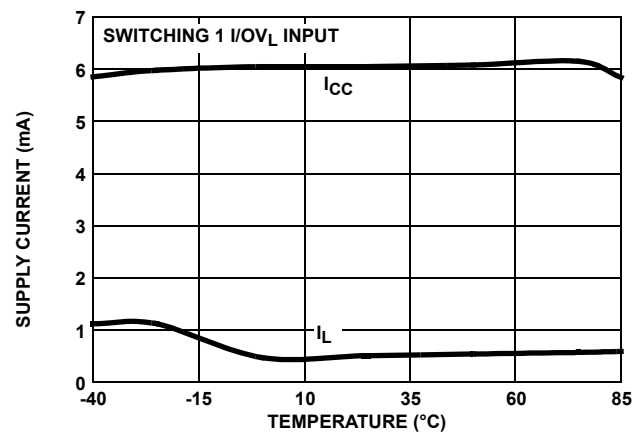


FIGURE 16. SUPPLY CURRENT vs TEMPERATURE

Typical Performance Curves

$V_{CC} = 3.3V$, $V_L = 1.8V$, $C_L = 15pF$, $R_{SOURCE} = 150\Omega$, data rate = 100Mbps, push-pull driver, $T_A = +25^\circ C$; unless otherwise specified. (Continued)

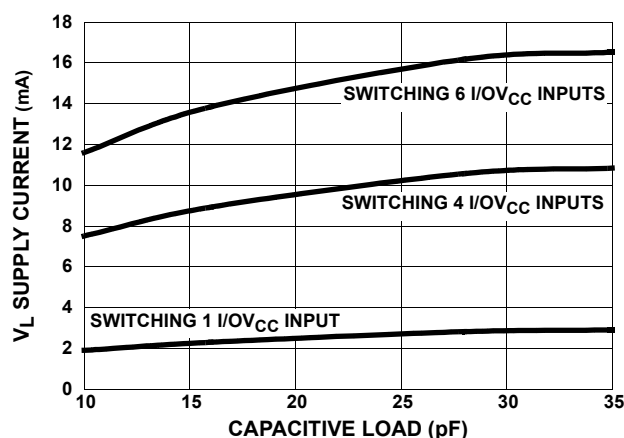


FIGURE 17. V_L SUPPLY CURRENT vs I/OV_L CAPACITIVE LOAD

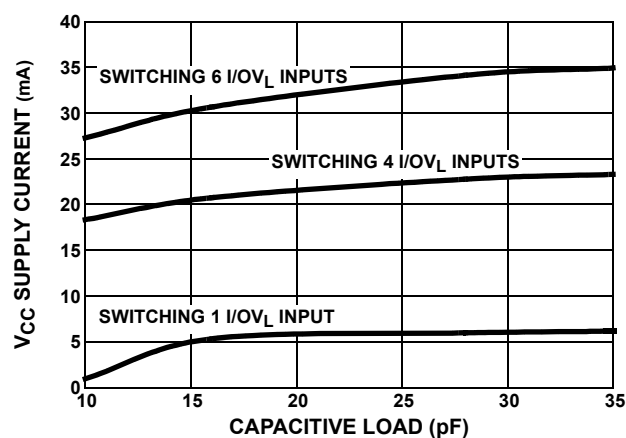


FIGURE 18. V_{CC} SUPPLY CURRENT vs I/OV_{CC} CAPACITIVE LOAD

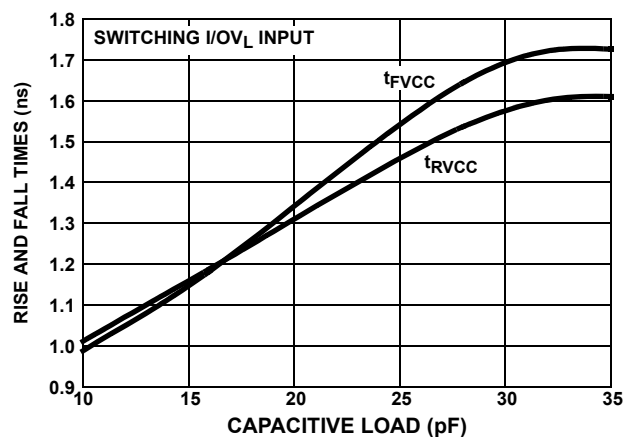


FIGURE 19. RISE/FALL TIME vs I/OV_{CC} CAPACITIVE LOAD

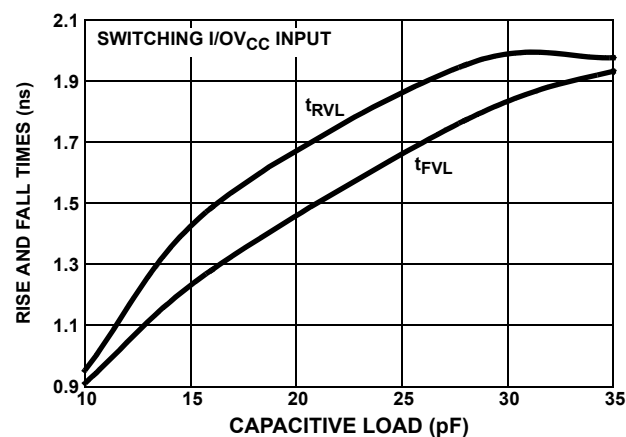


FIGURE 20. RISE/FALL TIME vs I/OV_L CAPACITIVE LOAD

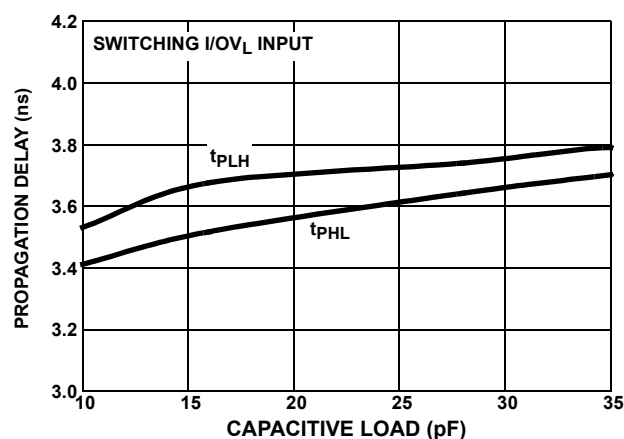


FIGURE 21. PROPAGATION DELAY vs I/OV_{CC} CAPACITIVE LOAD

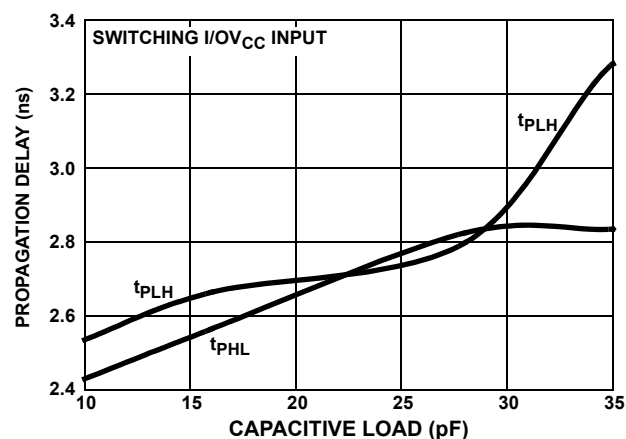


FIGURE 22. PROPAGATION DELAY vs I/OV_L CAPACITIVE LOAD

Typical Performance Curves

$V_{CC} = 3.3V$, $V_L = 1.8V$, $C_L = 15pF$, $R_{SOURCE} = 150\Omega$, data rate = 100Mbps, push-pull driver, $T_A = +25^\circ C$; unless otherwise specified. (Continued)

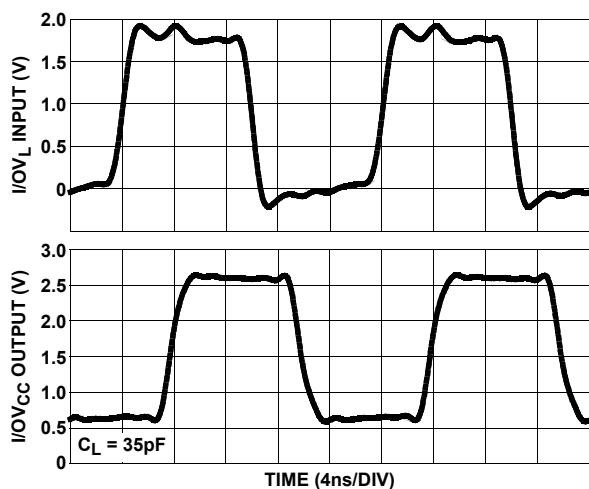


FIGURE 23. I/OV_{CC} OUTPUT WAVEFORMS (100Mbps)

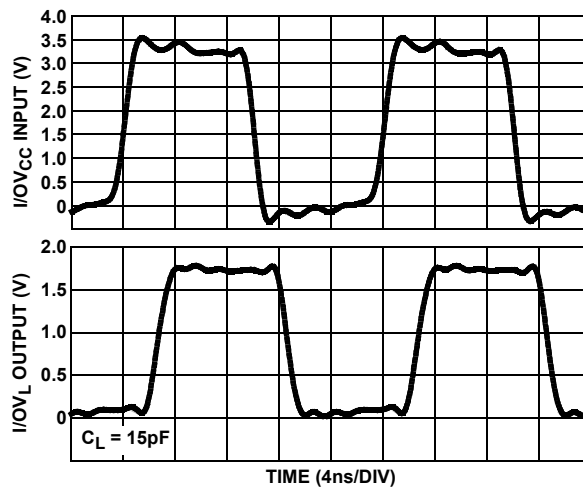


FIGURE 24. I/OV_L OUTPUT WAVEFORMS (100Mbps)

Die Characteristics

Substrate and QFN Thermal Pad Potential (Powered Up):

GND

Transistor Count:

2600

Process:

Si Gate BiCMOS

Revision History

The revision history provided is for informational purposes only and is believed to be accurate, but not warranted. Please visit our website to make sure you have the latest revision.

DATE	REVISION	CHANGE
Nov 7, 2019	FN6492.2	Updated links throughout. Added "Unidirectional Level Translator with Heavy Loading" section. Updated disclaimer
May 3, 2018	FN6492.1	Removed information about obsolete ISL3035E and ISL3036E devices. Updated datasheet title. Added Related Literature section on page 1. Updated Figure 1. Added Note 4 and tape and reel quantity column to Ordering Information table on page 2. Updated Package Outline Drawing L16.3x3A on page 12 to latest revision. Changes from previous version are as follows: Updated to new format (removed dimensions table), added land pattern Updated Package Outline Drawing L16.2.6x1.8A on page 13 to latest revision. Changes from previous version are as follows: Changed value in Note 5 from 0.30mm to 0.25mm. Removed Package Outline Drawing L14.3.5x3.5. Added Revision History. Applied new header/footer and added new Renesas disclaimer.
Mar 31, 2009	FN6492.0	Initial release.

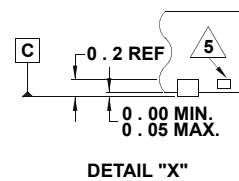
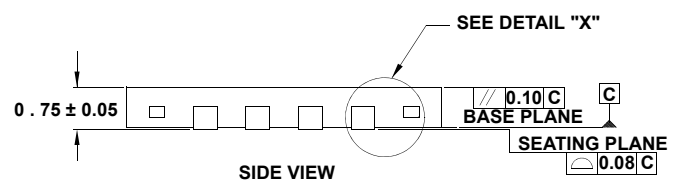
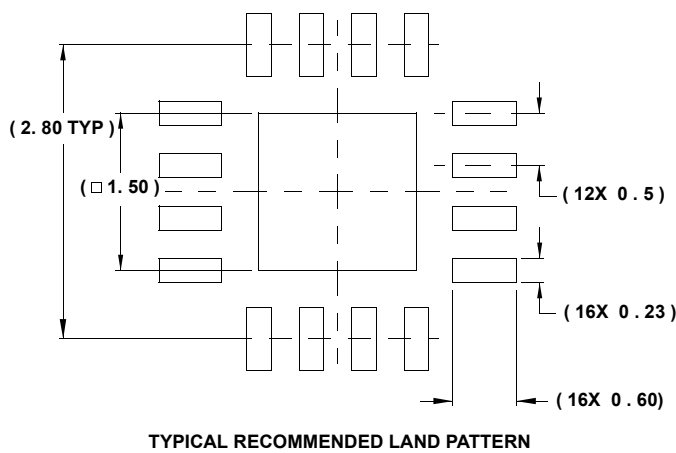
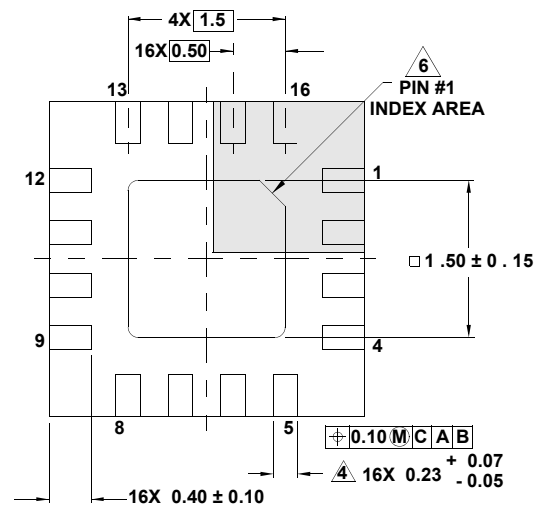
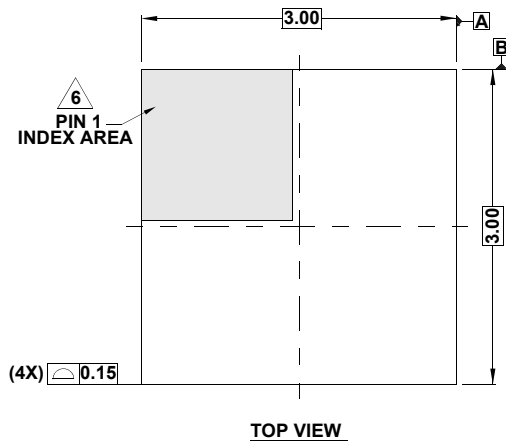
Package Outline Drawings

For the most recent package outline drawing, see [L16.3x3A](#).

L16.3x3A

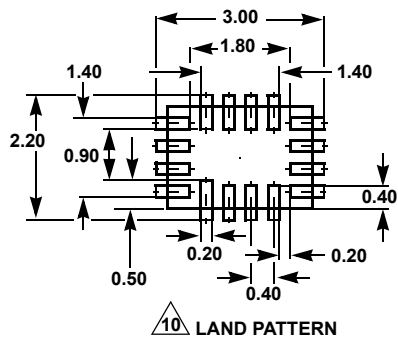
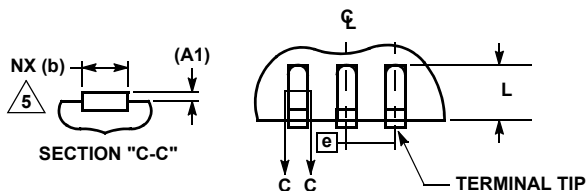
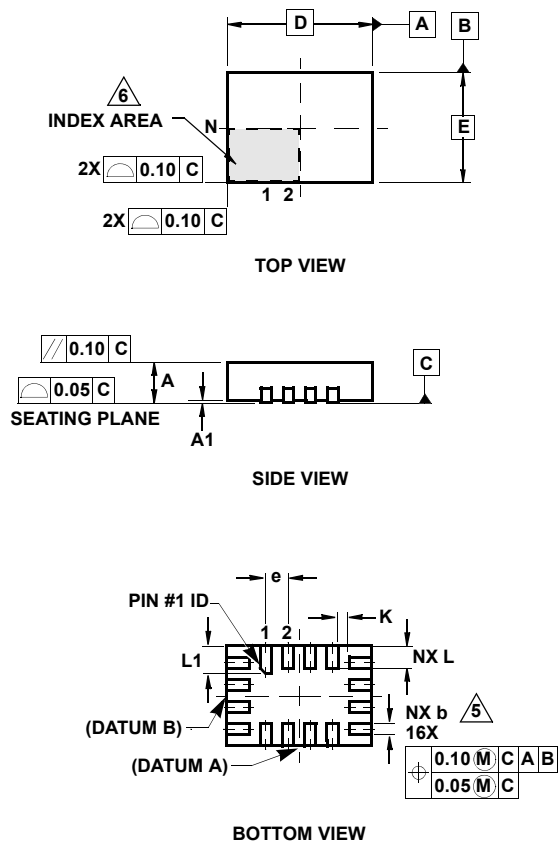
16 LEAD THIN QUAD FLAT NO-LEAD PLASTIC PACKAGE

Rev 1, 7/11



NOTES:

- Dimensions are in millimeters.
Dimensions in () for Reference Only.
- Dimensioning and tolerancing conform to AMSE Y14.5m-1994.
- Unless otherwise specified, tolerance: Decimal ± 0.05
- Dimension applies to the metallized terminal and is measured between 0.15mm and 0.30mm from the terminal tip.
- Tiebar shown (if present) is a non-functional feature.
- The configuration of the pin #1 identifier is optional, but must be located within the zone indicated. The pin #1 identifier may be either a mold or mark feature.



L16.2.6x1.8A
16 LEAD ULTRA THIN QUAD FLAT NO-LEAD PLASTIC PACKAGE

SYMBOL	MILLIMETERS			NOTES
	MIN	NOMINAL	MAX	
A	0.45	0.50	0.55	-
A1	-	-	0.05	-
A3	0.127 REF			-
b	0.15	0.20	0.25	5
D	2.55	2.60	2.65	-
E	1.75	1.80	1.85	-
e	0.40 BSC			-
K	0.15	-	-	-
L	0.35	0.40	0.45	-
L1	0.45	0.50	0.55	-
N	16			2
Nd	4			3
Ne	4			3
θ	0	-	12	4

Rev. 6 1/14

NOTES:

1. Dimensioning and tolerancing conform to ASME Y14.5-1994.
2. N is the number of terminals.
3. Nd and Ne refer to the number of terminals on D and E side, respectively.
4. All dimensions are in millimeters. Angles are in degrees.
5. Dimension b applies to the metallized terminal and is measured between 0.15mm and 0.25mm from the terminal tip.
6. The configuration of the pin #1 identifier is optional, but must be located within the zone indicated. The pin #1 identifier may be either a mold or mark feature.
7. Maximum package warpage is 0.05mm.
8. Maximum allowable burrs is 0.076mm in all directions.
9. JEDEC Reference MO-255.
10. For additional information, to assist with the PCB Land Pattern Design effort, see Technical Brief TB389.

For the most recent package outline drawing, see [L16.2.6x1.8A](#).

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(Rev.4.0-1 November 2017)

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